

2SK2980

Silicon N Channel MOS FET High Speed Power Switching

REJ03G1061-0400

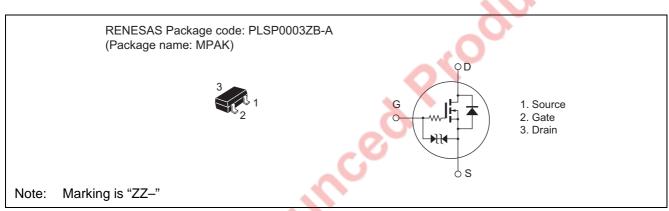
(Previous: ADE-208-571B)

Rev.4.00 Sep 07, 2005

Features

- Low on-resistance $R_{DS(on)} = 0.2 \; \Omega \; typ. \; (V_{GS} = 4 \; V, \, I_D = 500 \; mA)$
- 2.5 V gate drive devices.
- Small package (MPAK)

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V_{GSS}	+12	V
		-10	V
Drain current	I _D	1.0	A
Drain peak current	I _{D(pulse)} Note1	4	A
Channel dissipation	Pch Note2	0.8	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

2. Value at when using alumina ceramic board (12.5 x 20 x 0.7 mm)

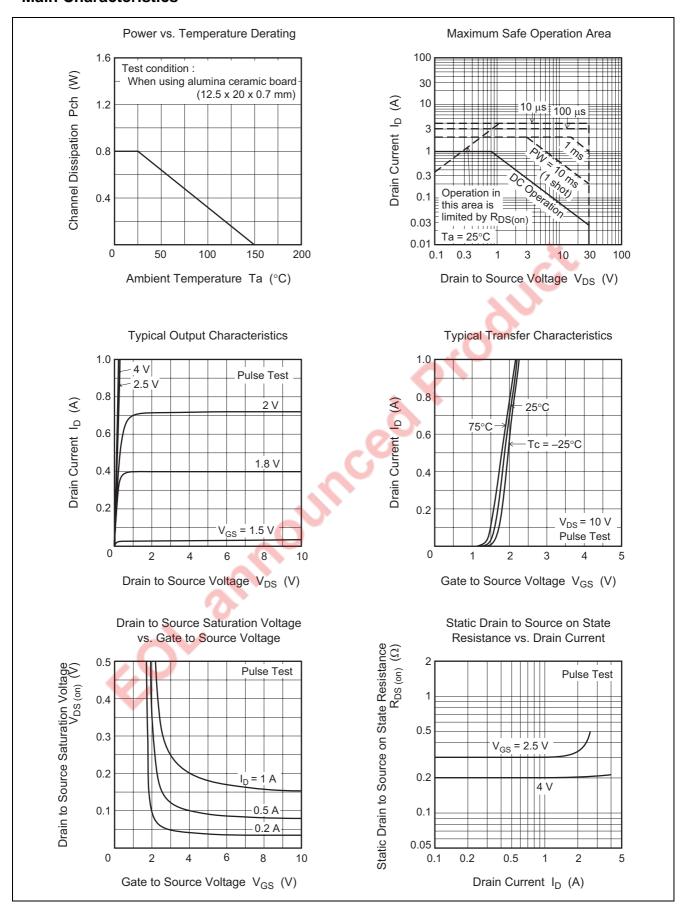
Electrical Characteristics

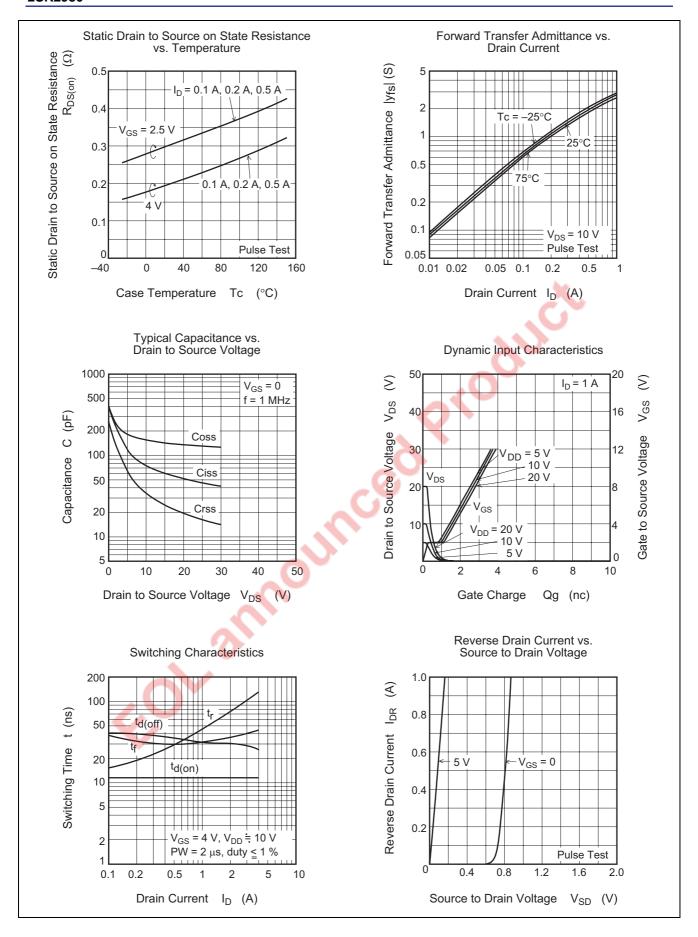
 $(Ta = 25^{\circ}C)$

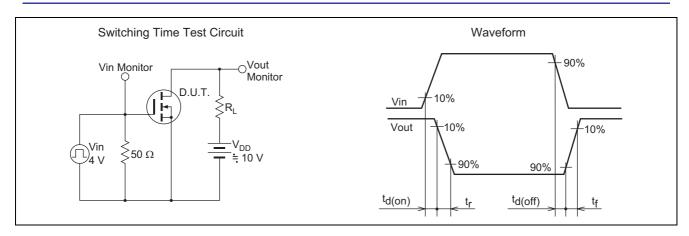
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 100 \mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	+12	_	_	V	$I_G = +100 \mu A, V_{DS} = 0$
		-10	_		V	$I_G = -100 \ \mu A, \ V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±5.0	μΑ	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.5	_	1.5	V	$I_D = 10 \mu A, V_{DS} = 5 V$
Static drain to source on state	R _{DS(on)}	_	0.2	0.28	Ω	$I_D = 500 \text{ mA}, V_{GS} = 4 \text{ V}^{\text{Note3}}$
resistance				9		
Static drain to source on state	R _{DS(on)}	_	0.3	0.5	Ω	$I_D = 500 \text{ mA}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$
resistance		4				
Forward transfer admittance	y _{fs}	1.2	2.0	_	S	$I_D = 500 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss		155	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	0	75	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss		35	_	pF	
Turn-on delay time	t _{d(on)}	_	12	_	ns	$V_{GS} = 4 \text{ V}, I_D = 500 \text{ mA},$
Rise time	t _r	_	30	_	ns	$R_L = 20 \Omega$
Turn-off delay time	t _{d(off)}	_	35	_	ns	
Fall time	t _f	_	30	_	ns	

Note: 3. Pulse test

Main Characteristics

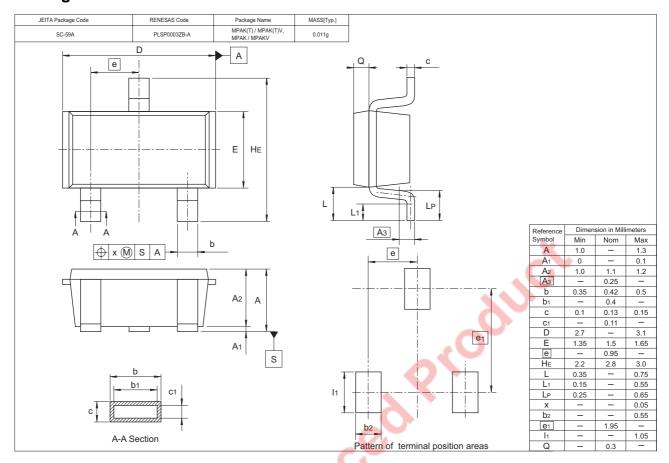








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK2980ZZ-TL-E	3000 pcs	Taping
2SK2980ZZ-TR-E	3000 pcs	Taping

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